

## SOT-89 Plastic-Encapsulate Transistors

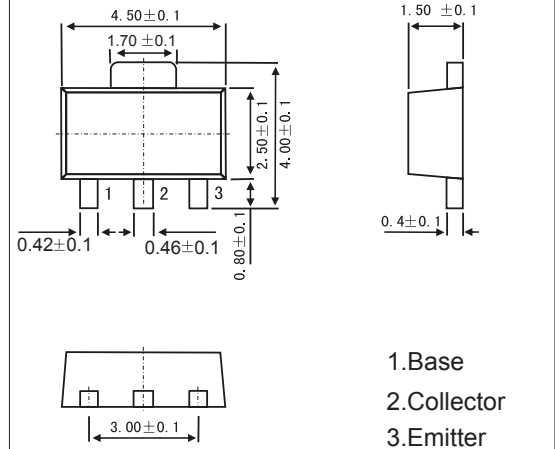
### Features

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A
- PNP Transistors

### MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any

SOT-89



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-60	V
Collector - Emitter Voltage	$V_{CE0}$	-60	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-600	mA
Collector Power Dissipation	$P_C$	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
PXT2907A (KXT2907A)	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_C = -1\text{ mA}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{CE0}$	$I_C = -10\text{ mA}, I_B = 0$	-60			
Emitter-base breakdown voltage	$V_{EB0}$	$I_E = -1\text{ mA}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$			-50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$			-1.6	V
		$I_C = -500\text{ mA}, I_B = -15\text{ mA}$			-0.4	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$			-2.6	
		$I_C = -500\text{ mA}, I_B = -15\text{ mA}$			-1.3	
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{ V}, I_C = -0.1\text{ mA}$	75			
	$h_{FE(2)}$	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}$	100			
	$h_{FE(3)}$	$V_{CE} = -10\text{ V}, I_C = -10\text{ mA}$	100			
	$h_{FE(4)}$	$V_{CE} = -10\text{ V}, I_C = -150\text{ mA}$	100		300	
	$h_{FE(5)}$	$V_{CE} = -10\text{ V}, I_C = -500\text{ mA}$	50			
Delay time	$t_d$	$V_{CC} = -30\text{ V}, I_C = -150\text{ mA}$ $I_{B1} = -I_{B2} = -15\text{ mA}$			12	ns
Rise time	$t_r$				30	
Storage time	$t_s$				300	
Fall time	$t_f$				65	
Transition frequency	$f_T$		$V_{CE} = -10\text{ V}, I_C = -20\text{ mA}, f = 100\text{ MHz}$	200		

### Marking

Marking	*2F
---------	-----